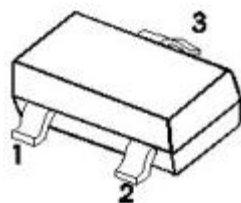


Features

- 开关速度小于 6nS; Fast Switching Device (TRR <6nS)
- 最大功率耗散 225mW; Power Dissipation of 225mW.
- 高稳定性和可靠性。High Stability and High Reliability.
- 反向漏电流小。Low reverse leakage.
- 封装: SOT-23 封装 SOT-23 Small Outline Plastic Package.
- 环氧树脂 UL 易燃等级 Epoxy UL: 94V-0.
- 安装位置: 任意 Mounting Position: Any



极限值和温度特性(TA = 25°C 除非另有规定)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
反向电压 Reverse Voltage	V _R	100	V
功率消耗 Power Dissipation	P _d	225	mW
工作结温 Operating junction temperature	T _j	150	°C
存储温度 Storage temperature range	T _s	-65-+ 150	°C
平均整流电流 Average Rectified Current	I _o	200	mA
正向(不重复)电流 Non-repetitive Peak Forward Current	I _{FM}	400	mA
正向(不重复)浪涌电流 Peak Forward Surge Current @tp= 1us; TA=25°C	I _{FSM}	2.0	A
典型热阻 Typical thermal resistance	R _{θJA}	500	°C/W

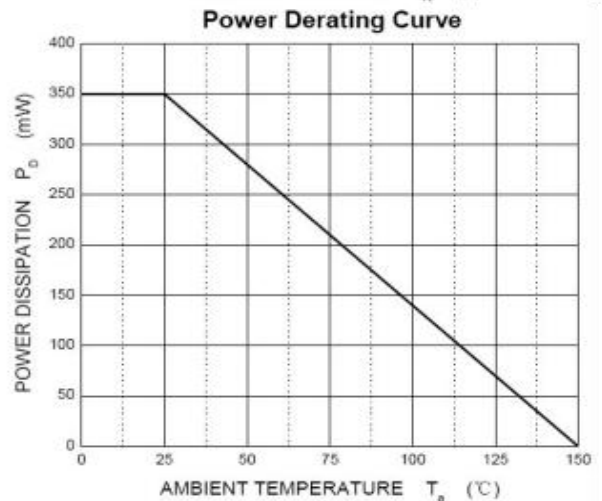
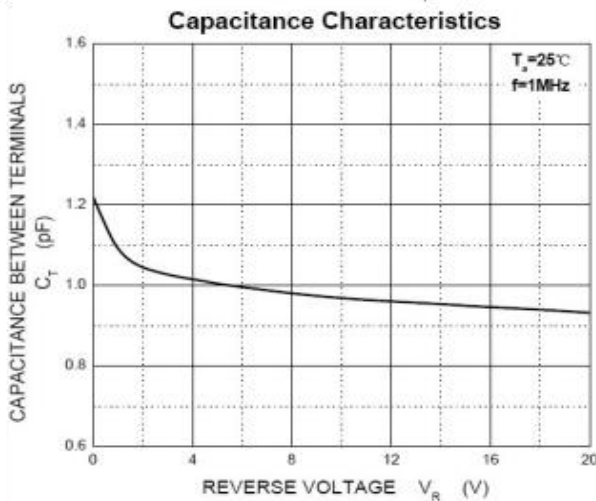
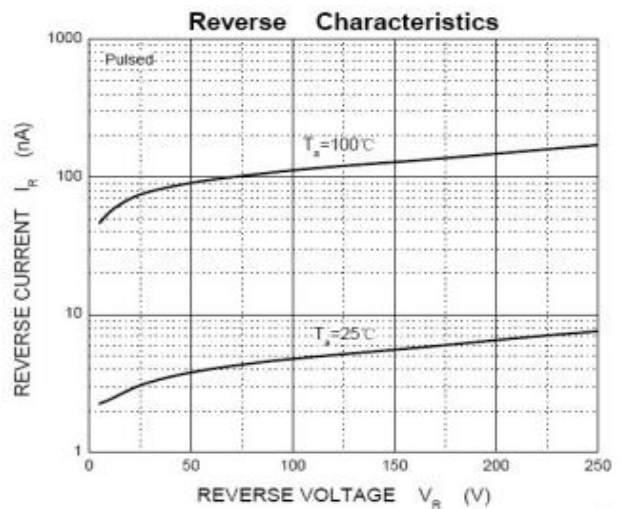
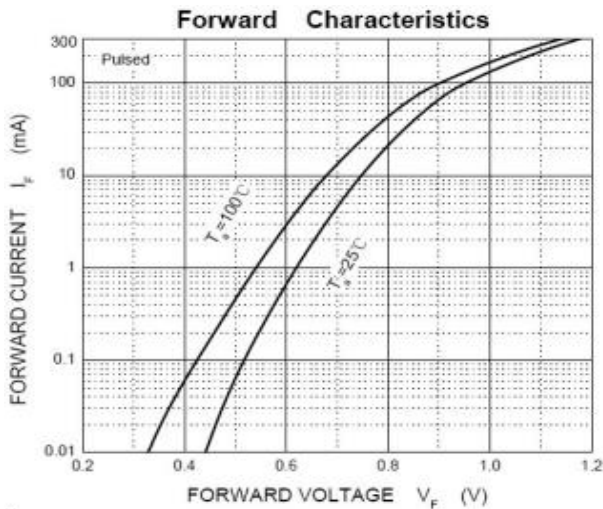
Valid provided that electrodes are kept at ambient temperature.



电特性 Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

符号 Symbols	参数 Parameter	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
VRB	反向击穿电压 Reverse Voltage	$I_B = 100\mu A$	100	---	V
IR	反向漏电流 Reverse Leakage Current	$V_R = 100V$	---	2.5	μA
VF	正向电压 Forward Voltage	$I_F = 1mA$	---	0.715	V
		$I_F = 10mA$	---	0.855	
		$I_F = 50mA$	---	1.00	
		$I_F = 150mA$	---	1.25	
TRR	反向恢复时间 Reverse Recovery Time	$I_F = I_R = 10mA, R_L = 100\Omega, I_{RR} = 0.1 I_R$	---	6	nS
CT	结电容 Capacitance	$V_R = 0V, f = 1MHz$	---	1.5	pF

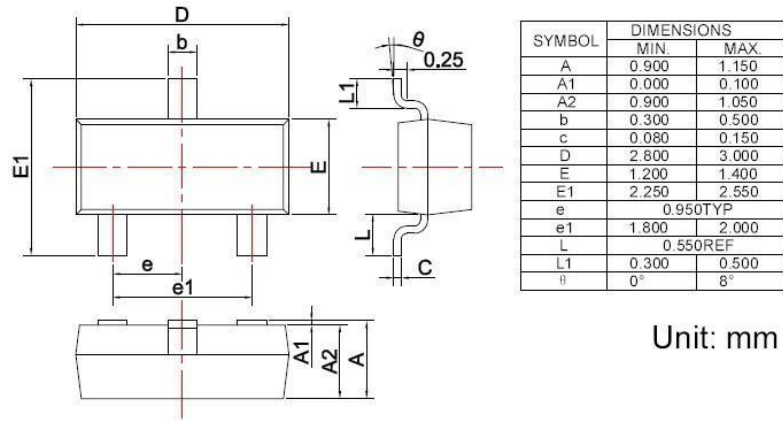
Typical Characteristics



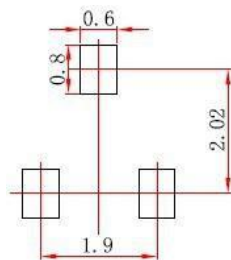


SOT-23 PACKAGE OUTLINE

Plastic surface mounted package



焊盘设计参考 Precautions: PCB Design(Recommended land dimensions for SOT-23 diode. Electrode patterns for PCBs)



- Note:
1. Controlling dimension; in millimeters.
 2. General tolerance: ±0.05mm.
 3. The pad layout is for reference purposes only.